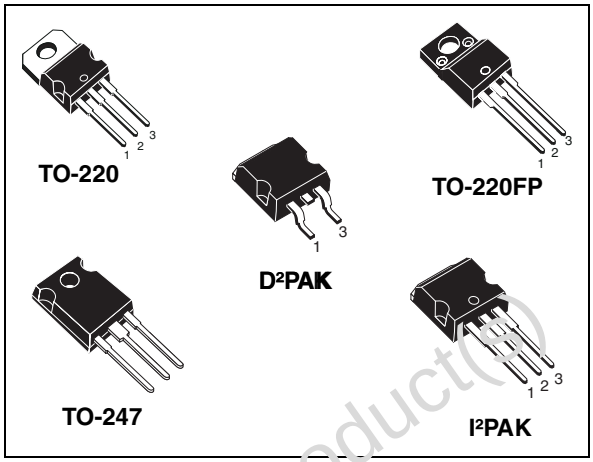
STB12NM50FD - STB12NM50FD-1
STP12NM50FD/FP - STW14NM50FD

N-channel 500V - 0.32Ω - 12A - TO-220/FP - D²/I²PAK - TO-247
FDmesh™ Power MOSFET (with fast diode)

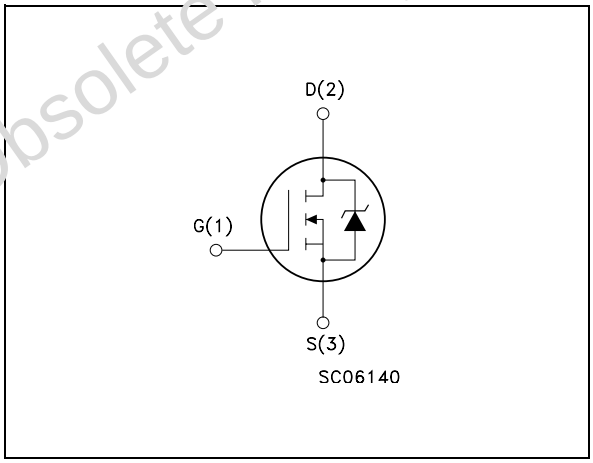
General features

Type	V_{DSS}	$R_{DS(on)}$	I_D	Pw
STB12NM50FD	500V	<0.4Ω	12A	160W
STB12NM50FD-1	500V	<0.4Ω	12A	160W
STP12NM50FD	500V	<0.4Ω	12A	160W
STP12NM50FDFP	500V	<0.4Ω	12A	35W
STW14NM50FD	500V	<0.4Ω	12A	160W

- 100% avalanche tested
- High dv/dt and avalanche capabilities
- Low input capacitance and gate charge
- Low gate input resistance
- Tight process control and high manufacturing yields



Internal schematic diagram



Description

The FDmesh™ associates all advantages of reduced on-resistance and fast switching with an intrinsic fast-recovery body diode. It is therefore strongly recommended for bridge topologies, in particular ZVS phase-shift converters.

Applications

- Switching application

Order codes

Part number	Marking	Package	Packaging
STB12NM50FD	B12NM50FD	D²PAK	Tape & reel
STB12NM50FD-1	B12NM50FD	I²PAK	Tube
STP12NM50FD	P12NM50FD	TO-220	Tube
STP12NM50FDFP	P12NM50FDFP	TO-220FP	Tube
STW14NM50FD	W14NM50FD	TO-247	Tube

Obsolete Product(s) - Obsolete Product(s)

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2 Electrical characteristics 5

2.1 Electrical characteristics (curves) 6

3 Test circuit 10

4 Package mechanical data 11

5 Packaging mechanical data 17

6 Revision history 18

Obsolete Product(s) - Obsolete Product(s)

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value			Unit
		TO-220/ D²/I²PAK	TO-220FP	TO-247	
V_{DS}	Drain-source voltage (V_{GS} = 0)	500			V
V_{DGR}	Drain-gate voltage (R_{GS} = 20KΩ)	500			V
V_{GS}	Gate-source voltage	± 30			V
I_D	Drain current (continuous) at T_C = 25°C	12	12(1)	14	A
I_D	Drain current (continuous) at T_C=100°C	7.5	7.5(1)	8.8	A
I_{DM}(2)	Drain current (pulsed)	48	48 (1)	56	A
P_{TOT}	Total dissipation at T_C = 25°C	160	35	160	W
	Derating factor	1.28	0.28	1.4	W/°C
dv/dt(3)	Peak diode recovery voltage slope	20			V/ns
V_{ISO}	Insulation withstand voltage (DC)	--	2500	--	V
T_J T_{stg}	Operating junction temperature Storage temperature	-65 to 150			°C

1. Limited only by maximum temperature allowed
2. Pulse width limited by safe operating area
3. I_{SD} ≤12A, di/dt ≤400A/µs, V_{DD} =80%$V_{(BR)DSS}$

Table 2. Thermal resistance

Symbol	Parameter	Value				Unit
		TO-220 I²PAK	D²PAK	TO-220FP	TO-247	
$R_{thj\text{-}case}$	Thermal resistance junction-case Max	0.78		3.57	0.77	°C/W
$R_{thj\text{-}a}$	Thermal resistance junction-ambient Max	62.5	100	62.5		°C/W
T_l	Maximum lead temperature for soldering purpose	300				°C

Table 3. Avalanche data

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by Tj Max)	6	A
E_{AS}	Single pulse avalanche energy (starting Tj=25°C, Id=Iar, Vdd=50V)	400	mJ

Obsolete Product(s) - Obsolete Product(s)

2 Electrical characteristics

(T_{CASE}=25°C unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test condictions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	I_D = 1mA, V_{GS}= 0	500			V
I_{DSS}	Zero gate voltage drain current (V_{GS} = 0)	V_{DS} = Max rating, V_{DS} = Max rating @125°C			1 10	µA µA
I_{GSS}	Gate body leakage current (V_{DS} = 0)	V_{GS} = ±30V			±100	nA
$V_{GS(th)}$	Gate threshold voltage	V_{DS}= V_{GS}, I_D = 250µA	3	4	5	V
$R_{DS(on)}$	Static drain-source on resistance	V_{GS}= 10V, I_D= 6A		0.32	0.4	Ω

Table 5. Dynamic

Symbol	Parameter	Test condictions	Min.	Typ.	Max.	Unit
g_{fs} (1)	Forward transconductance	V_{DS} =15V, I_D = 6A		9.8		S
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	V_{DS} =25V, f=1 MHz, V_{GS}=0		1000 390 20		pF pF pF
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	V_{DD}=400V, I_D = 3A V_{GS} =10V (see Figure 11)		12 3 7		nC nC nC
R_G	Gate input resistance	f=1 MHz Gate DC Bias= 0 test signal level = 20mV open drain		2		Ω

1. Pulsed: pulse duration=300µs, duty cycle 1.5%

Obsolete Product(s) - Obsolete Product(s)

Table 6. Switching times

Symbol	Parameter	Test Condictions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on delay time Rise time	V_{DD}=250 V, I_D= 6A, R_G=4.7Ω, V_{GS}=10V (see Figure 17)		19 10		ns ns
$t_{r(Voff)}$ t_f t_c	Off-voltage rise time Fall time Cross-over time	V_{DD}=400 V, I_D= 12A, R_G=4.7Ω, V_{GS}=10V (see Figure 17)		39 18 29		ns ns ns

Table 7. Source drain diode

Symbol	Parameter	Test condictions	Min	Typ.	Max	Unit
I_{SD}	Source-drain current				12	A
I_{SDM}(1)	Source-drain current (pulsed)				48	A
V_{SD}(2)	Forward on voltage	I_{SD}=12A, V_{GS}=0			1.5	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	I_{SD}=12A, Tj=25°C di/dt = 100A/µs, V_{DD}=30V, (see Figure 22)		140 800 11		ns nC A
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	I_{SD}=12A, Tj=150°C di/dt = 100A/µs, V_{DD}=30V, (see Figure 22)		252 1890 15		ns nC A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration=300µs, duty cycle 1.5%

Obsolete Product(s) - Obsolete Product(s)

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area for TO-220/ D²PAK/I²PAK

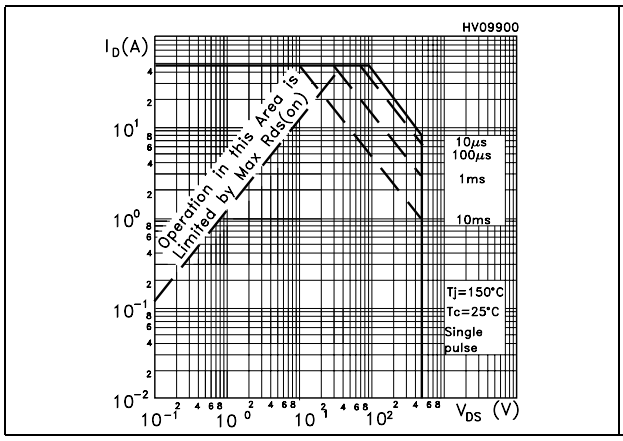


Figure 2. Thermal impedance for TO-220/ D²PAK/I²PAK

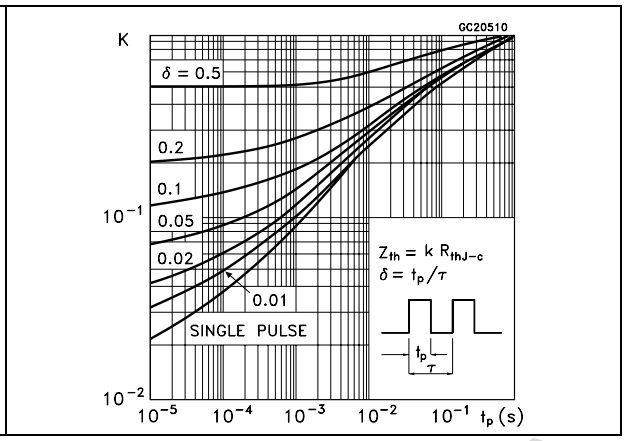


Figure 3. Safe operating areafor TO-220FP

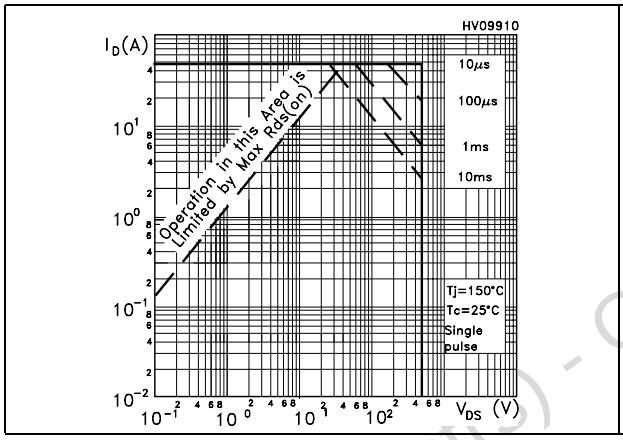


Figure 4. Thermal impedance for TO-220FP

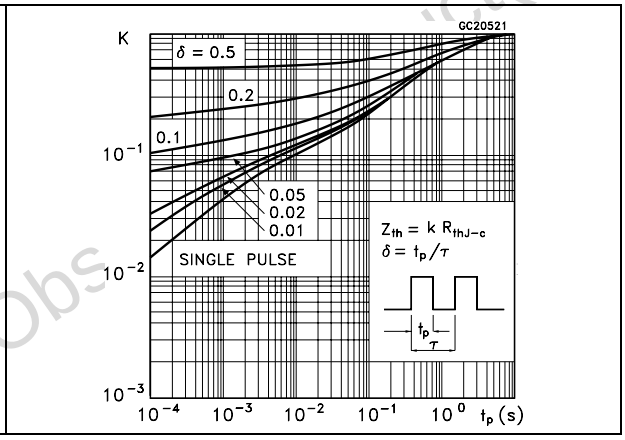


Figure 5. Safe operating area for TO-247

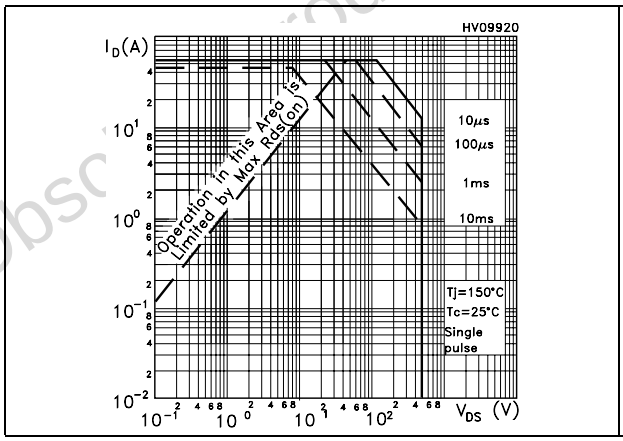
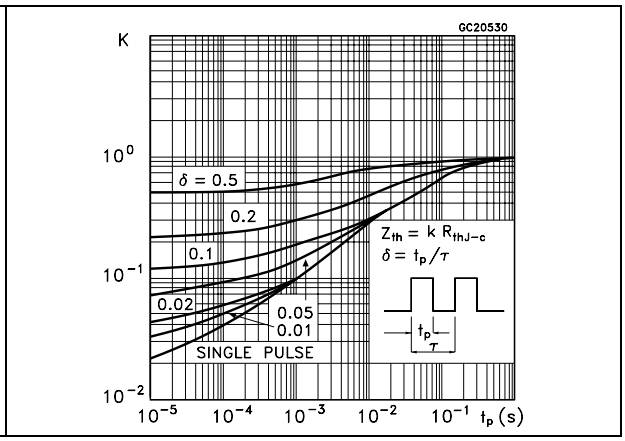


Figure 6. Thermal impedance for TO-247



Obsolete Product(s) - Obsolete Product(s)

Figure 7. Output characterisics

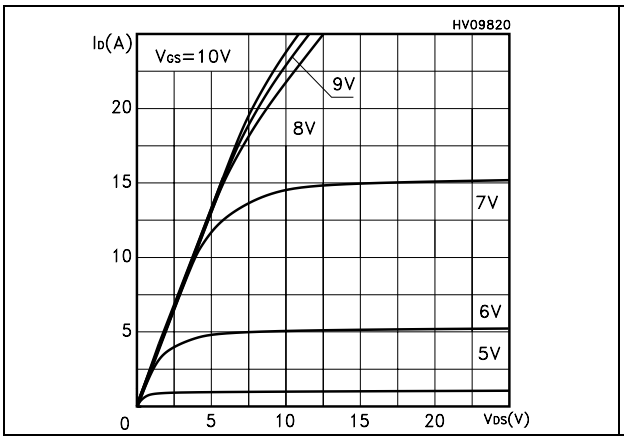


Figure 8. Transfer characteristics

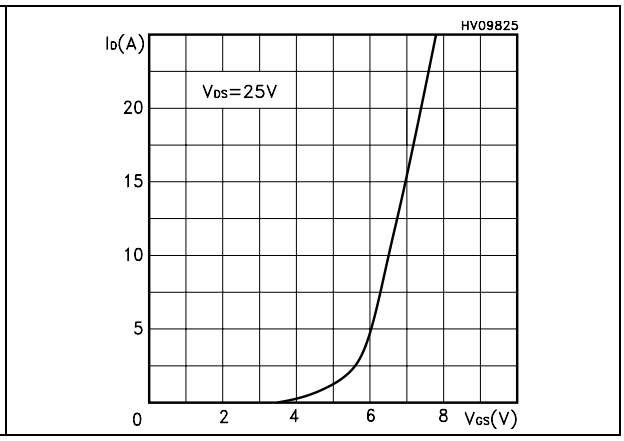


Figure 9. Transconductance

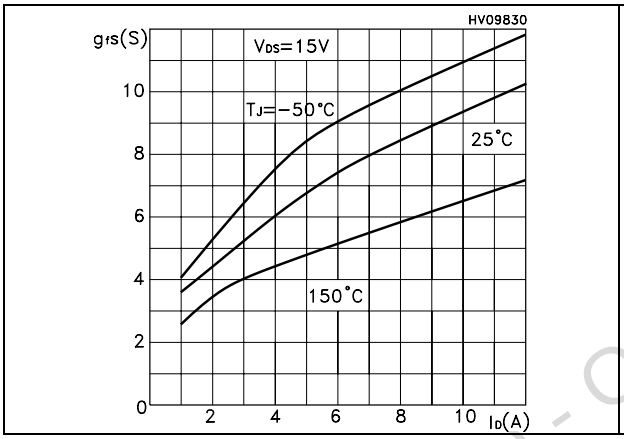


Figure 10. Static drain-source on resistance

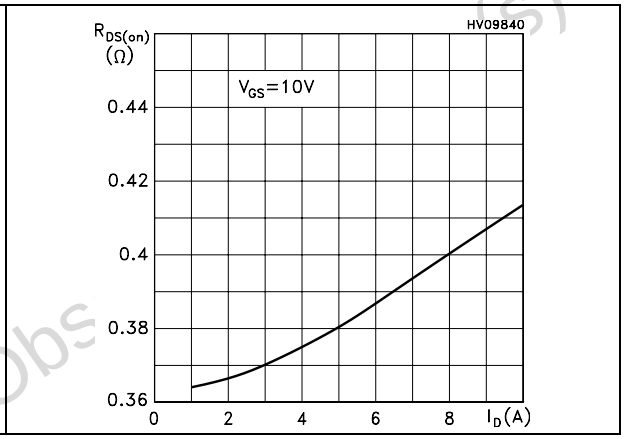


Figure 11. Gate charge vs gate-source voltage

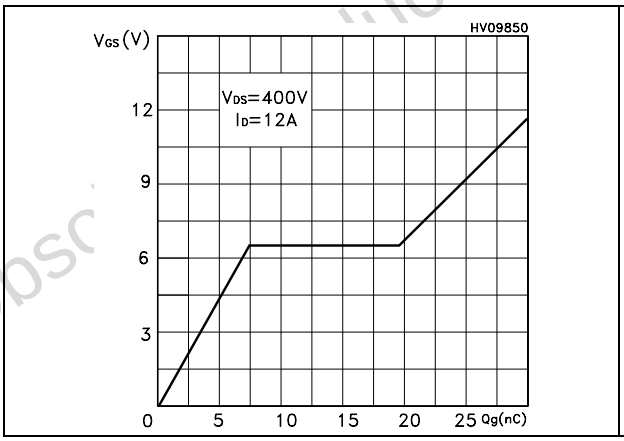


Figure 12. Capacitance variations

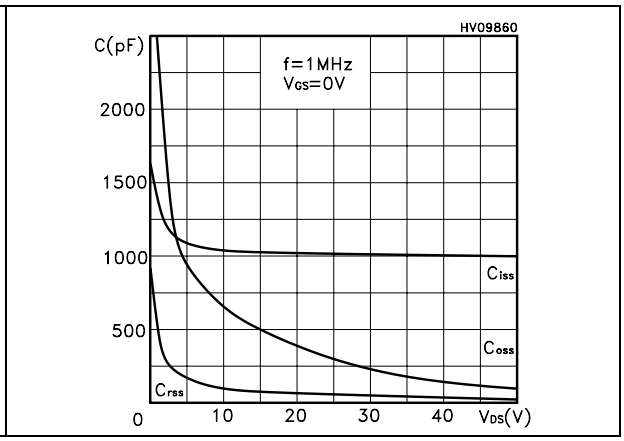


Figure 13. Normalized gate threshold voltage vs temperature

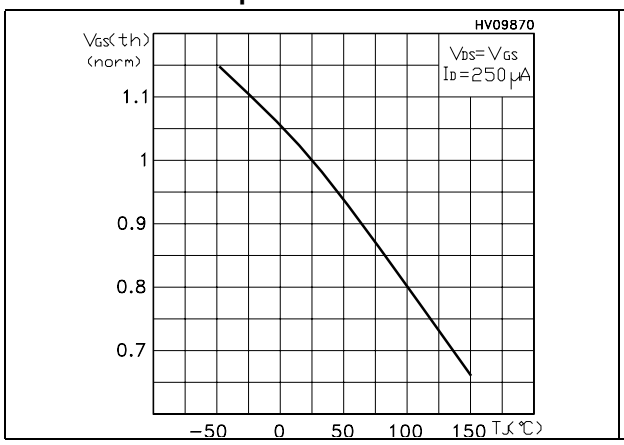


Figure 14. Normalized on resistance vs temperature

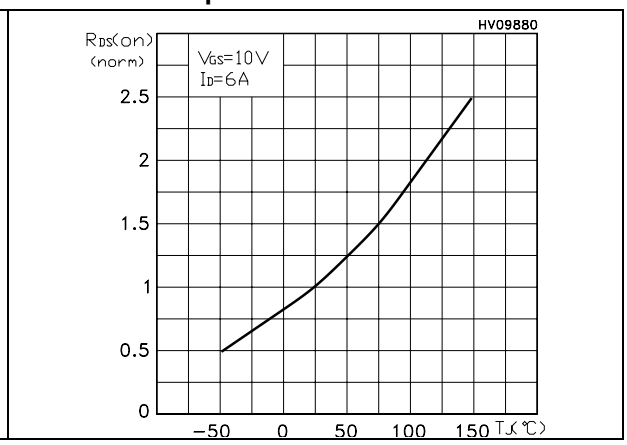


Figure 15. Source-drain diode forward characteristics

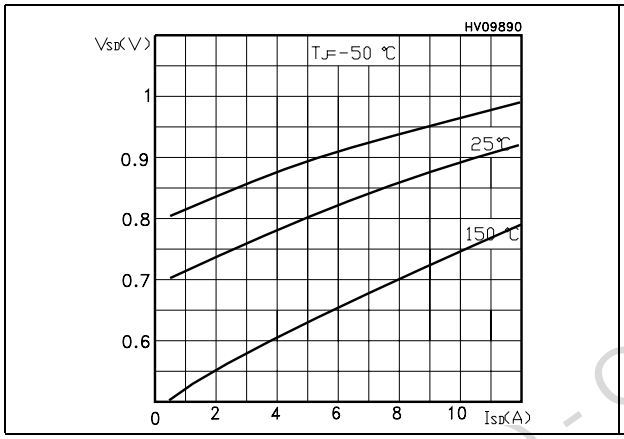
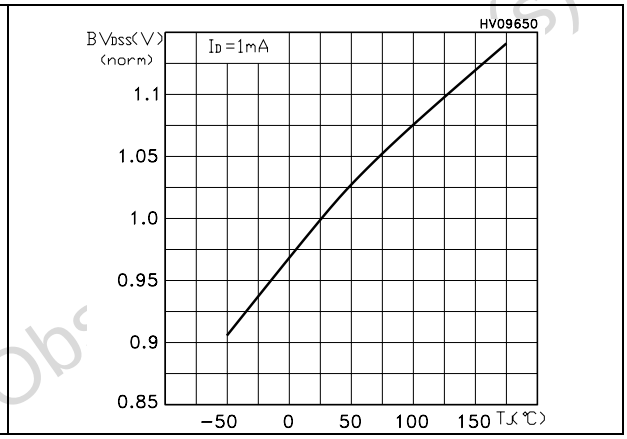


Figure 16. Normalized B_{VDSS} vs temperature



Obsolete Product(s) - Obs

3 Test circuit

Figure 17. Switching times test circuit for resistive load

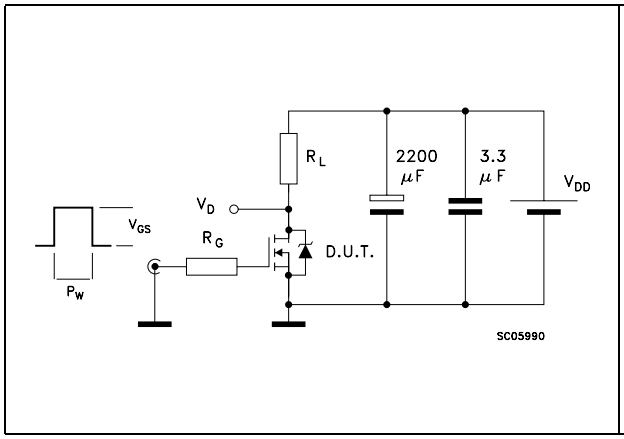


Figure 18. Gate charge test circuit

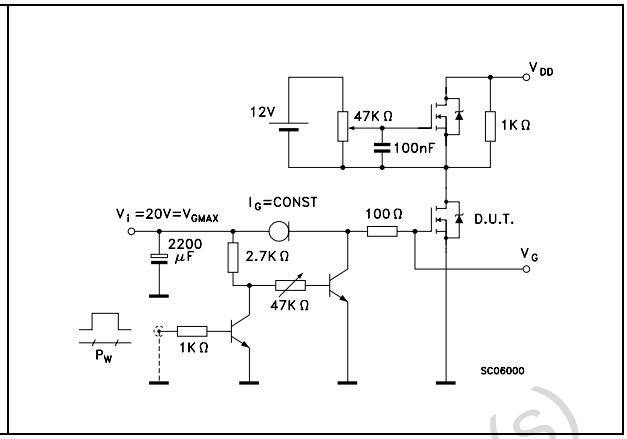


Figure 19. Test circuit for inductive load switching and diode recovery times

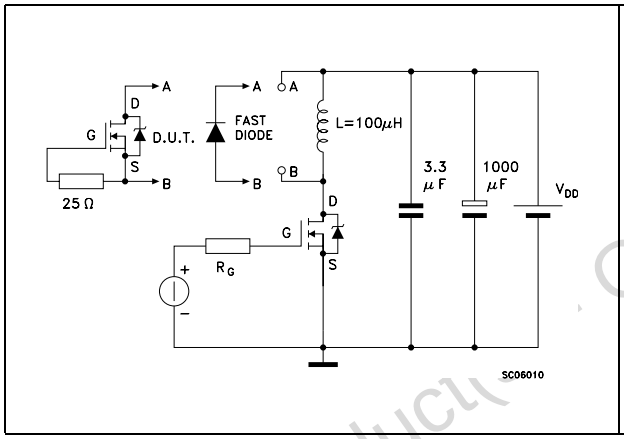


Figure 20. Unclamped inductive load test circuit

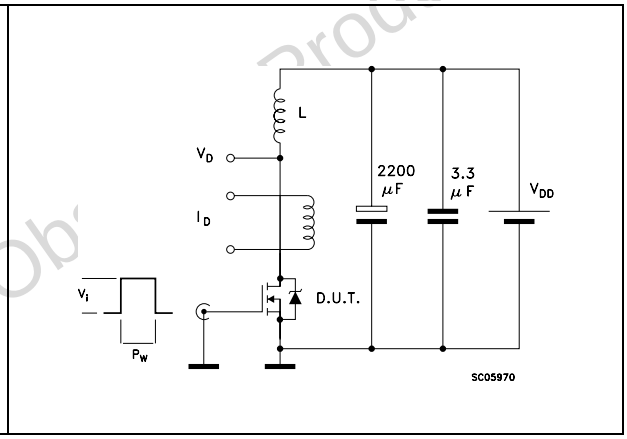


Figure 21. Unclamped inductive waveform

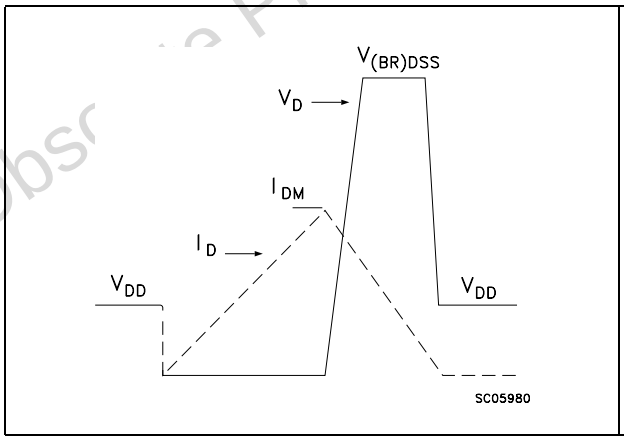
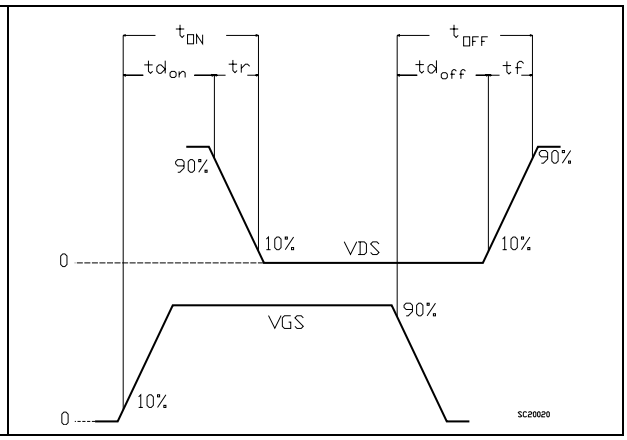


Figure 22. Switching time waveform



Obsolete Product(s) - Obsolete Product(s)

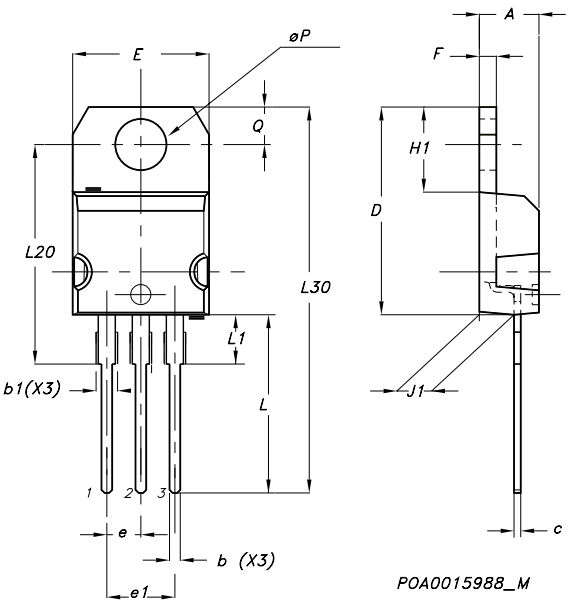
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at : *www.st.com*

Obsolete Product(s) - Obsolete Product(s)

TO-220 MECHANICAL DATA

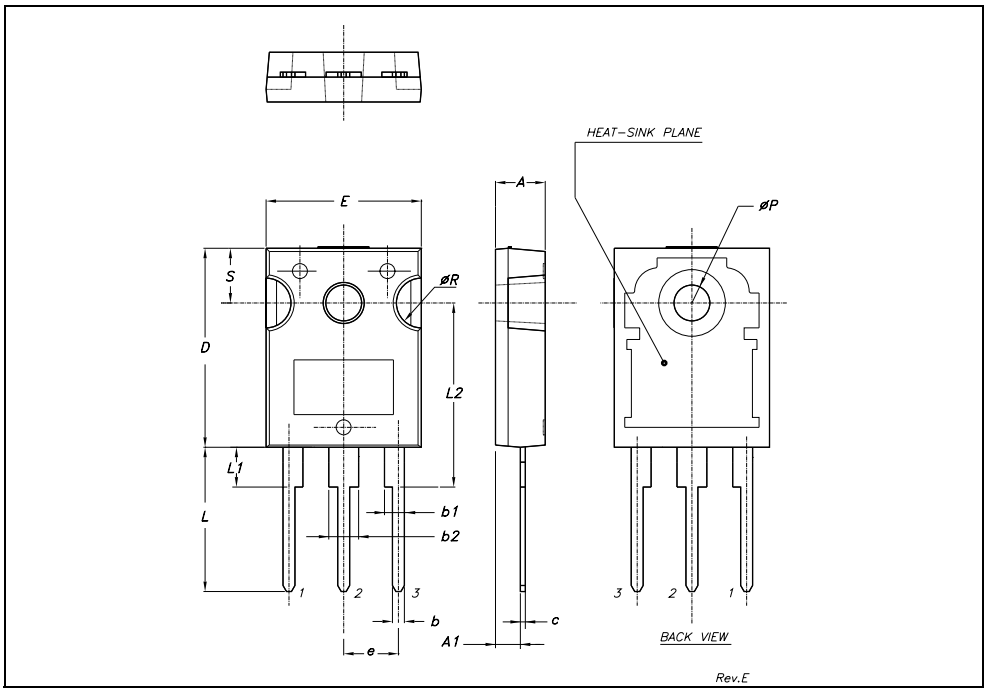
DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
øP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



Obsole

TO-247 MECHANICAL DATA

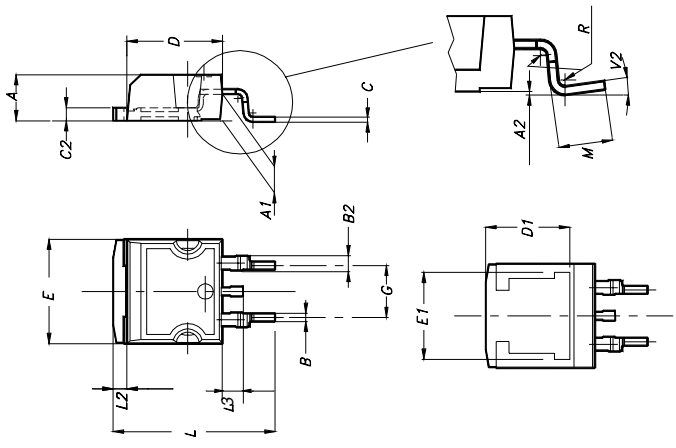
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b	1.0		1.40	0.039		0.055
b1	2.0		2.40	0.079		0.094
b2	3.0		3.40	0.118		0.134
c	0.40		0.80	0.015		0.03
D	19.85		20.15	0.781		0.793
E	15.45		15.75	0.608		0.620
e		5.45			0.214	
L	14.20		14.80	0.560		0.582
L1	3.70		4.30	0.14		0.17
L2		18.50			0.728	
øP	3.55		3.65	0.140		0.143
øR	4.50		5.50	0.177		0.216
S		5.50			0.216	



Obsole

D^2PAK MECHANICAL DATA

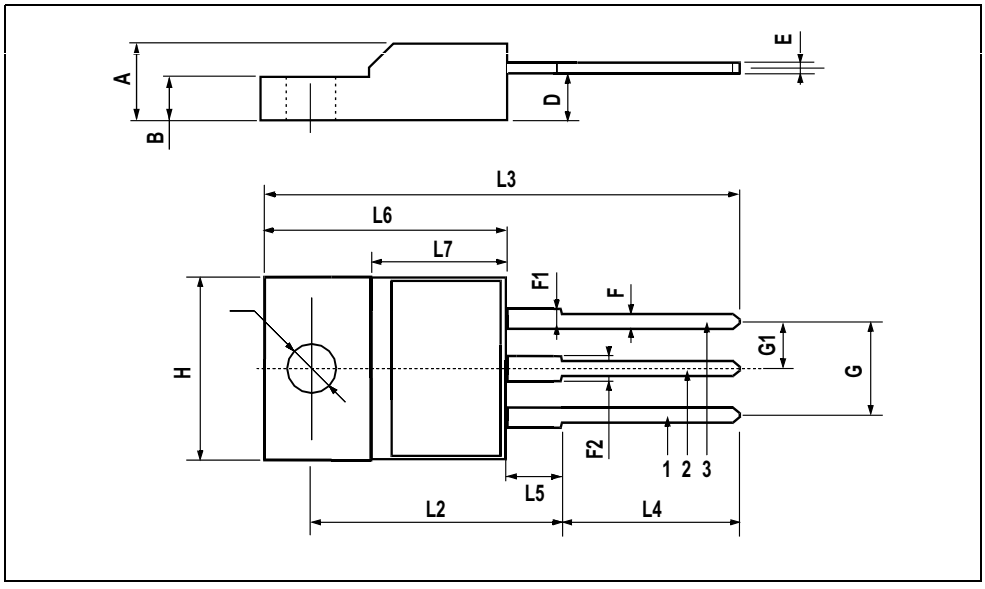
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A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0º		4º			



Obsole

TO-220FP MECHANICAL DATA

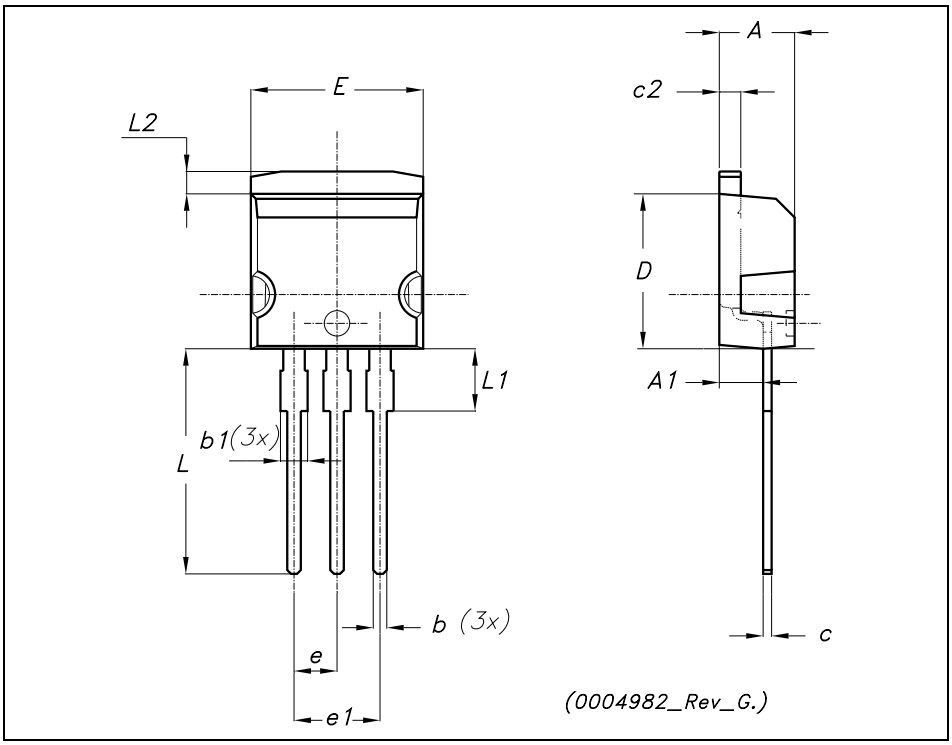
DIM.	mm.			inch		
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B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	.0385		0.417
L5	2.9		3.6	0.114		0.141
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



Obsole

TO-262 (I^2PAK) MECHANICAL DATA

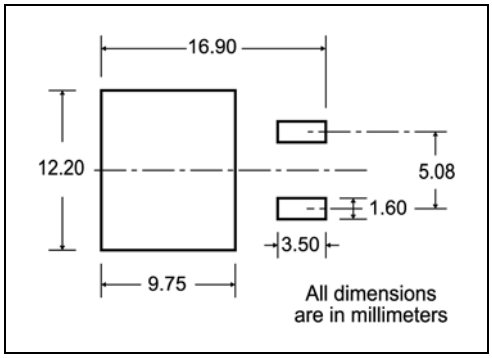
DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
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A1	2.40		2.72	0.094		0.107
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.49		0.70	0.019		0.027
c2	1.23		1.32	0.048		0.052
D	8.95		9.35	0.352		0.368
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
E	10		10.40	0.393		0.410
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L2	1.27		1.40	0.050		0.055



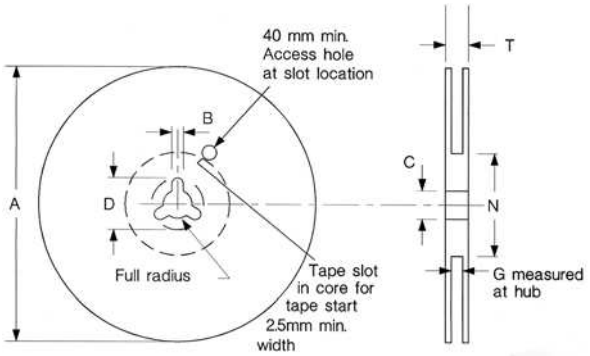
Obsole

5 Packaging mechanical data

D²PAK FOOTPRINT



TAPE AND REEL SHIPMENT



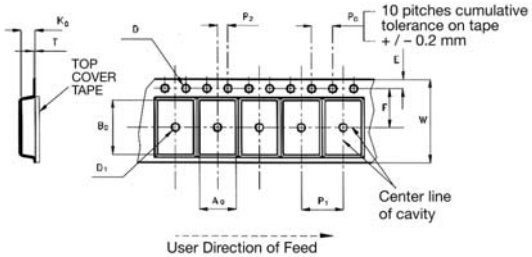
REEL MECHANICAL DATA

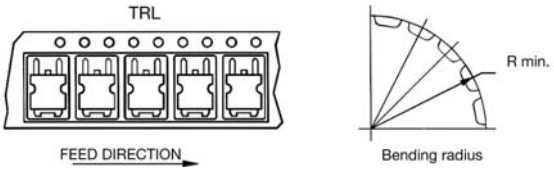
DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197

BASE QTY	BULK QTY
1000	1000

TAPE MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956





* on sales type

6 Revision history

Table 8. Revision history

Date	Revision	Changes
03-May-2006	3	New template

Obsolete Product(s) - Obsolete Product(s)

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